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|  | <p>SI2306BDS-T1-E3</p> |
| | <p>Hersteller-Teilenummer: SI2306BDS-T1-E3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET N-CH 30V 3.16A SOT23-3</p> <p>Datenblätter:  SI2306BDS-T1-E3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 58604 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p> |
| <p>Image may be representation. See specs for product details.</p> | |

Spezifikationen

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|---|---|
| Teilenummer | SI2306BDS-T1-E3 |
| Hersteller | Vishay / Siliconix |
| Beschreibung | MOSFET N-CH 30V 3.16A SOT23-3 |
| Kategorie | Diskrete Halbleiterprodukte > Transistoren-FETs , |
| Teilstatus | 58604 pcs Stock |
| Serie | TrenchFET® |
| Technologie | MOSFET (Metal Oxide) |
| Betriebstemperatur | -55°C ~ 150°C (TJ) |
| Befestigungsart | Surface Mount |
| Verpackung / Gehäuse | TO-236-3, SC-59, SOT-23-3 |
| Supplier Device-Gehäuse | SOT-23-3 (TO-236) |
| Verlustleistung (max) | 750mW (Ta) |
| Typ FET | N-Channel |
| FET-Merkmal | - |
| Drain-Source-Spannung (Vdss) | 30V |
| Strom - Ununterbrochener Abfluss (Id) bei 25 °C | 3.16A (Ta) |
| Rds On (Max) @ Id, Vgs | 47 mOhm @ 3.5A, 10V |
| VGS (th) (Max) @ Id | 3V @ 250µA |
| Gate Charge (Qg) (Max) @ Vgs | 4.5nC @ 5V |
| Eingabekapazität (Ciss) (Max) @ Vds | 305pF @ 15V |
| Antriebsspannung (Max Rds On, Min Rds On) | 4.5V, 10V |
| Vgs (Max) | ±20V |
| Verpackung | Tape & Reel (TR) |










SI2306BDS-T1-E3 ist neu im Original, Suche SI2306BDS-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2306BDS-T1-E3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI2306BDS-T1-E3: Info@Y-IC.com

Sie können auch interessiert sein:

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|  <p>SI2306BDS-T1 VISHAY SI2306BDS-T1 VISHAY</p> |  <p>SI2306CDS-T1-E3 VISHAY SI2306CDS-T1-E3 VISHAY</p> |  <p>SI2306BDS-T1-GE3 Vishay / Siliconix MOSFET N-CH 30V 3.16A SOT23-3</p> |  <p>SI2306/AO3406 UTC UTC SOT-23</p> |
|  <p>SI2306BDS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 3.16A SOT23-3</p> |  <p>SI2306BDS VISHAY SI2306BDS VISHAY</p> |  <p>SI2306-TP Micro Commercial Components (MCC) N-CHANNEL MOSFET, SOT-23 PACKAGE</p> |  <p>SI2306 A6SHB Original SOT-23</p> |

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|  SI2304DDS-T1-GE3 |  SI2304DS |  SI2304DS-T1 |  SI2304DS-T1-E3 |  SI2304DS-T1-GE3 |
|  SI2305-CDS-T1-GE3 |  SI2305ADS-T1-E3 |  SI2305ADS-T1-E3 |  SI2305ADS-T1-GE3 |  SI2305ADS-T1-GE3 |
|  SI2305BDS-T1-E3 |  SI2305BDS-T1-GE3 |  SI2305CDS-T1-E3 |  SI2305CDS-T1-GE3 |  SI2305CDS-T1-GE3 |
|  SI2305DS |  SI2305DS-E3 |  SI2305DS-T1 |  SI2305DS-T1-E3 |  SI2305DS-T1-E3 |
|   SI2305DS-T1-GE3 |  SI2305WCB |  SI2306BDS |  SI2306BDS-T1 |  SI2306BDS-T1-E3 |
|   SI2306BDS-T1-GE3 |   SI2306BDS-T1-GE3 |  SI2306CDS-T1-E3 |  SI2306DS |  SI2306DS-T1 |
|   SI2306DS-T1-E3 |  SI2306DS-T1-GE3 |   SI2306WCA |   SI2307BDS |   SI2307BDS-T1-E3 |
|   SI2307BDS-T1-E3 |   SI2307BDS-T1-GE3 |   SI2307BDS-T1-GE3 |   SI2307CDS |   SI2307CDS-T1-E3 |
|   SI2307CDS-T1-E3 |   SI2307CDS-T1-GE3 |   SI2307CDS-T1-GE3 |  SI2307DS |   SI2307DS-T1 |
|   SI2307DS-T1-E3 |   SI2307DS-T1-GE3 |   SI2307DS-T7-E3 |  SI2308BDS |   SI2308BDS-T1-E3 |

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